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Vishay Semiconductors

# Medium Power Phase Control Thyristors (Stud Version), 50 A



PRIMARY CHARACTERISTICS				
I <sub>T(AV)</sub>	50 A			
V <sub>DRM</sub> /V <sub>RRM</sub>	100 V, 200 V, 400 V, 600 V, 800 V, 1000 V, 1200 V			
$V_{TM}$	1.60 V			
I <sub>GT</sub>	100 mA			
TJ	-40 °C to 125 °C			
Package	TO-65 (TO-208AC)			
Circuit configuration	Single SCR			

#### **FEATURES**

- High current rating
- Excellent dynamic characteristics
- dV/dt = 1000 V/µs option
- Superior surge capabilities
- Standard package
- · Metric threads version available
- Types up to 1200 V V<sub>DRM</sub>/V<sub>RRM</sub>
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **TYPICAL APPLICATIONS**

- · Phase control applications in converters
- · Lighting circuits
- Battery charges
- Regulated power supplies and temperature and speed control circuit

PARAMETER	TEST CONDITIONS	VALUES	UNITS	
1		50	A	
I <sub>T(AV)</sub>	T <sub>C</sub>	94	°C	
I <sub>T(RMS)</sub>		80	A	
I <sub>TSM</sub>	50 Hz	1430	Α	
	60 Hz	1490		
<sup>2</sup> t	50 Hz	10.18	kA <sup>2</sup> s	
1-1	60 Hz	9.30	- KA2S	
V <sub>DRM</sub> /V <sub>RRM</sub>		100 to 1200	V	
t <sub>q</sub>	Typical	110	μs	
TJ		-40 to +125	°C	

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE <sup>(1)</sup> V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE <sup>(2)</sup> V	$\begin{aligned} I_{DRM}/I_{RRM} & \text{MAXIMUM AT} \\ & T_J = T_J & \text{MAXIMUM} \\ & \text{mA} \end{aligned}$			
	10	100	150				
	20	200	300				
	40	400	500				
VS-50RIA	60	600	700	15			
	80	800	900				
	100	1000	1100				
	120	1200	1300				

#### Notes

<sup>(1)</sup> Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs

 $<sup>\</sup>ensuremath{^{(2)}}$  For voltage pulses with  $t_p \leq 5 \ ms$ 



PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average on-state current at case temperature	I <sub>T(AV)</sub>	180° sinusoidal conduction		50	A	
·					94	°C
Maximum RMS on-state current	I <sub>T(RMS)</sub>				80	Α
		t = 10 ms	No voltage		1430	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		1490	^
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		1200	A
		t = 8.3 ms	reapplied	Sinusoidal half wave,	1255	
Maximum I <sup>2</sup> t for fusing		t = 10 ms	No voltage	initial $T_J = T_J$ maximum	10.18	kA <sup>2</sup> s
	l <sup>2</sup> t	t = 8.3 ms	reapplied		9.30	
		t = 10 ms	100 % V <sub>BRM</sub>		7.20	
		t = 8.3 ms	reapplied		6.56	
Maximum I²√t for fusing	I <sup>2</sup> √t	$t = 0.1$ to 10 ms, no voltage reapplied, $T_J = T_J$ maximum		101.8	kA²√s	
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x $\pi$ x I <sub>T(AV)</sub> < I < $\pi$ x I <sub>T(AV)</sub> ), T <sub>J</sub> = T <sub>J</sub> maximum		0.94	V	
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(\pi \times I_{T(AV)} < I$	$(\pi \times I_{T(AV)} < I < 20 \times \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			V
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $I_{T(AV)}$ < $I$ < $\pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum			4.08	mΩ
High level value of on-state slope resistance	r <sub>t2</sub>	$(\pi \times I_{T(AV)} < I < 20 \times \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$ 3.34			11152	
Maximum on-state voltage	V <sub>TM</sub>	I <sub>pk</sub> = 157 A, T <sub>J</sub> = 25 °C			1.60	V
Maximum holding current	I <sub>H</sub>	$T_J$ = 25 °C, anode supply 22 V, resistive load, initial $I_T$ = 2 A		200	mA	
Latching current	ΙL				400	

SWITCHING							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum rate of	$V_{DRM} \le 600 \text{ V}$	$T_C$ = 125 °C, $V_{DM}$ = Rated $V_{DRM}$ , $T_C$ = 0.1 μs maximum dI/dt Gate pulse = 20 V, 15 $\Omega$ , $t_p$ = 6 μs, $t_r$ = 0.1 μs maximum		dI/dt	dI/dt	200	A/µs
rise of turned-on current V	$V_{DRM} \le 1600 \text{ V}$	di/dt	$I_{TM} = (2 \text{ x rated dI/dt}) \text{ A}$	100	7/μ5		
Typical delay time		t <sub>d</sub>	$t_{\rm d}$ $T_{\rm C}$ = 25 °C, $V_{\rm DM}$ = Rated $V_{\rm DRM}$ , $I_{\rm TM}$ = 10 A dc resistive circuit Gate pulse = 10 V, 15 $\Omega$ source, $t_{\rm p}$ = 20 $\mu$ s		.10		
Typical turn-off time $t_{\rm q} = \frac{T_{\rm C} = 125~^{\circ}{\rm C}, \ l_{\rm TM} = 50~{\rm A, reapplied~dV/dt} = 20~{\rm V/\mu s}}{{\rm dlr/dt} = -10~{\rm A/\mu s, \ V_R} = 50~{\rm V}}$		110	μs				

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum critical rate of rise of	d\//dt	$T_J = T_J$ maximum linear to 100 % rated $V_{DRM}$	200	\//uo	
off-state voltage	dV/dt	T <sub>J</sub> = T <sub>J</sub> maximum linear to 67 % rated V <sub>DRM</sub>	500 <sup>(1)</sup>	V/µs	

#### Note

 $<sup>^{(1)}</sup>$  Available with dV/dt = 1000 V/ $\mu s$ , to complete code add S90 i.e. 50RIA120S90



TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak gate power	P <sub>GM</sub>	$T_J = T_J$ maximum, $t_p \le 5$	$T_J = T_J$ maximum, $t_p \le 5$ ms		w
Maximum average gate power	P <sub>G(AV)</sub>				VV
Maximum peak positive gate current	I <sub>GM</sub>			2.5	Α
Maximum peak positive gate voltage	+V <sub>GM</sub>			20	V
Maximum peak negative gate voltage	-V <sub>GM</sub>			10	1 v
	I <sub>GT</sub>	T <sub>J</sub> = - 40 °C	Maximum required gate trigger current/voltage are the lowest value which will trigger all units 6 V	250	mA
DC gate current required to trigger		T <sub>J</sub> = 25 °C		100	
		T <sub>J</sub> = 125 °C		50	
DC	.,,	T <sub>J</sub> = - 40 °C	anode to cathode applied	3.5	V
DC gate voltage required to trigger	$V_{\rm GT}$	T <sub>J</sub> = 25 °C		2.5	
DC gate current not to trigger	I <sub>GD</sub>	$T_J = T_J$ maximum, $V_{DRM} = Rated voltage$	Maximum gate current/voltage not to trigger is the maximum	5.0	mA
DC gate voltage not to trigger	$V_{GD}$	$T_J = T_J$ maximum	value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.2	V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-40 to +125	°C	
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation		K/W	
Maximum thermal resistance, case to heat sink	R <sub>thCS</sub>	Mounting surface, smooth, flat and greased	0.25	1 N/VV	
Allowable requesting toyour		Non-lubricated threads	3.4 + 0 - 10 % (30)	N⋅m	
Allowable mounting torque		Lubricated threads	2.3 + 0 - 10 % (20)	(lbf·in)	
Approximate weight			28	g	
Approximate weight			1.0	oz.	
Case style		See dimensions - link at the end of datasheet TO-65 (TO		208AC)	

△R <sub>thJC</sub> CONDUCTION							
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS			
180°	0.078	0.057					
120°	0.094	0.098					
90°	0.120	0.130	$T_J = T_J$ maximum	K/W			
60°	0.176	0.183					
30°	0.294	0.296					

#### Note

The table above shows the increment of thermal resistance R<sub>thJC</sub> when devices operate at different conduction angles than DC

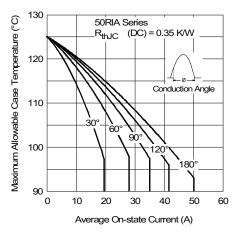


Fig. 1 - Current Ratings Characteristics

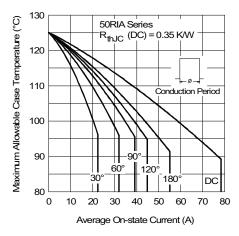


Fig. 2 - Current Ratings Characteristics

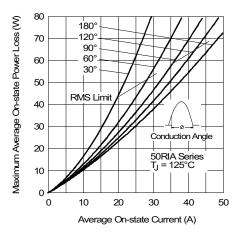


Fig. 3 - On-State Power Loss Characteristics

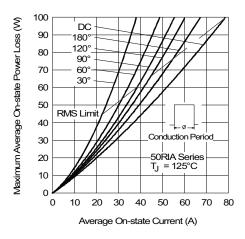


Fig. 4 - On-State Power Loss Characteristics

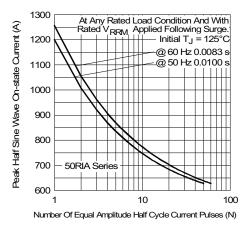


Fig. 5 - Maximum Non-Repetitive Surge Current

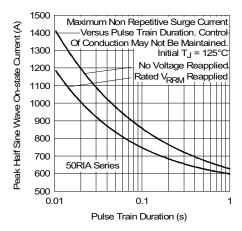


Fig. 6 - Maximum Non-Repetitive Surge Current

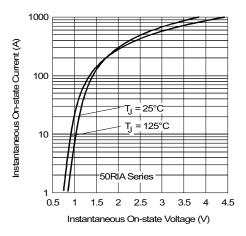


Fig. 7 - Forward Voltage Drop Characteristics

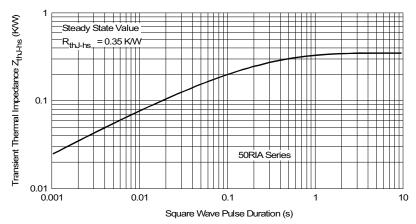


Fig. 8 - Thermal Impedance Z<sub>thJC</sub> Characteristics

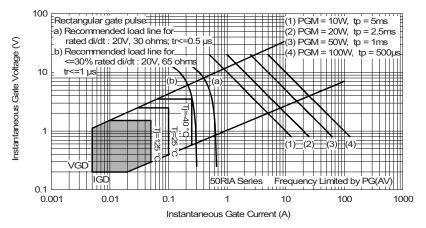
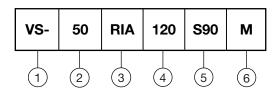


Fig. 9 - Gate Characteristics



#### **ORDERING INFORMATION TABLE**

#### Device code



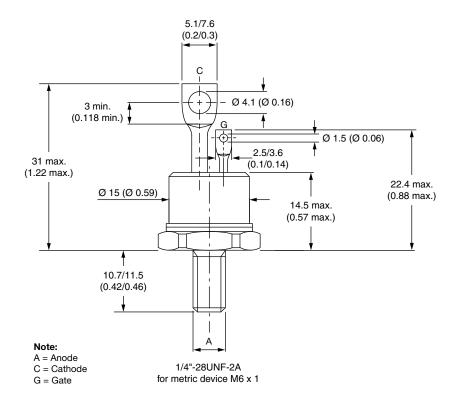
- Vishay Semiconductors product
- 2 Current code
- Essential part number
- Voltage code x 10 = V<sub>RRM</sub> (see Voltage Ratings table)
- 5 Critical dV/dt:
  - None = 500 V/µs (standard value)
  - S90 = 1000 V/µs (special selection)
- 6 • None = stud base TO-65 (TO-208AC) 1/4" 28UNF-2A
  - M = stud base TO-65 (TO-208AC) M6 x 1

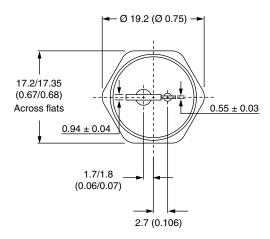
LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95334			



# TO-208AC (TO-65)

### **DIMENSIONS** in millimeters (inches)







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